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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10041026	FILING DATE 12/28/2001	CLASS 118	SUBCLASS 1734	GAU	EXAMINER Meek
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1762

**CONTINUING DATA VERIFIED:

** FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiners's initials			ATTORNEY DOCKET NO 006333
TITLE : Methods for silicon oxide and oxynitride deposition using single wafer low pressure CVD U.S.DEP.T. OF COMM./PAT. & TM.-PTO-436L(Rev. 12-94)			

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING		
Amount Due	Date Paid	Sheets Drwg.		Figs.Drwg.
		Print Fig.		
TERMINAL DISCLAIMER		Primary Examiner		
		Application Examiner		
PREPARED FOR ISSUE				
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